

P-Channel MOSFET MEM2309S

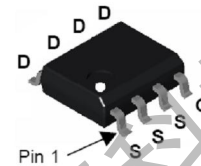
Description :

MEM2309SGSeries P-channel enhancement mode field-effect transistor ,produced with high cell density DMOS trench technology, which is especially used to minimize on-state resistance.

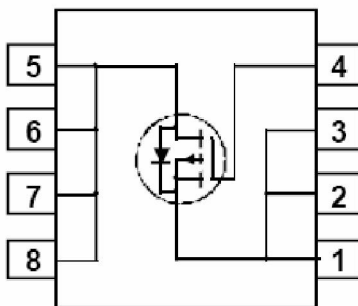
This device particularly suits low voltage applications, and low power dissipation.

Feature :

- | -30V/-6A
 $R_{DS(ON)} = 53m @ V_{GS} = -10V, I_D = -6A$
 $R_{DS(ON)} = 68m @ V_{GS} = -4.5V, I_D = -4A$
- | High Density Cell Design For Ultra Low On-Resistance
- | Surface mount package:SOP8



Pin Configuration :



Typical Application:

- | Power management
- | Load switch
- | Battery protection

Absolute Maximum Ratings:

Parameter	Symbol	Ratings	Unit	
Drain-Source Voltage	V_{DSS}	-30V	V	
Gate-Source Voltage	V_{GSS}	± 20	V	
Drain Current	I_D	$T_A = 25$	-6	A
		$T_A = 70$	-3.2	
Pulsed Drain Current ^{1,2}	I_{DM}	-30	A	
Total Power Dissipation	P_d	$T_A = 25$	2	W
		$T_A = 70$	0.8	
Operating Temperature Range	T_{Opr}	150		
Storage Temperature Range	T_{stg}	-65/150		

Thermal Characteristics:

Parameter	Symbol	Ratings	Unit
Thermal Resistance, Junction-to-Ambient ³	R JA	50	W

Electrical Characteristics:

MEM2309SG

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30	-34		V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.1	-1.3	-2	V
Gate-Body Leakage	I_{GSS}	$V_{DS}=0V, V_{GS}=20V$		-5	30	nA
		$V_{DS}=0V, V_{GS}=-20V$		-5	-30	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$		-6	-300	nA
Static Drain-Source On-Resistance	$R_{DS(ON)1}$	$V_{GS}=-10V, I_D=-6A$	33	53	65	m
	$R_{DS(ON)2}$	$V_{GS}=-4.5V, I_D=-4A$	50	68	80	m
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-5.3A$		10		S
Drain-Source Diode Forward Current	I_S				-2.1	A
Source-drain (diode forward) voltage	V_{SD}	$V_{GS}=0V, I_D=-1A$		-0.8	-1.2	V
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$		530		pF
Output Capacitance	C_{oss}			140		
Reverse Transfer Capacitance	C_{rss}			70		
Switching Characteristics						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=-15V, I_D=-1A, V_{GEN}=-10V, R_g=6$		8	15	ns
Rise Time	t_r			15	25	
Turn-Off Delay Time	$t_{d(off)}$			15	25	
Fall-Time	t_f			10	15	
Total Gate Charge	Q_g	$V_{DS}=-15V, V_{GS}=-10V, I_D=-4A$		10	15	nC
Gate-Source Charge	Q_{gs}			2.2		
Gate-Drain Charge	Q_{gd}			2.0		

- 1、Repetitive rating, pulse width limited by junction temperature.
- 2、Pulse test; pulse width 300 us, duty cycle 2%.
- 3、Surface Mounted on FR4 Board, t 10 sec.

Typical Performance Characteristics :

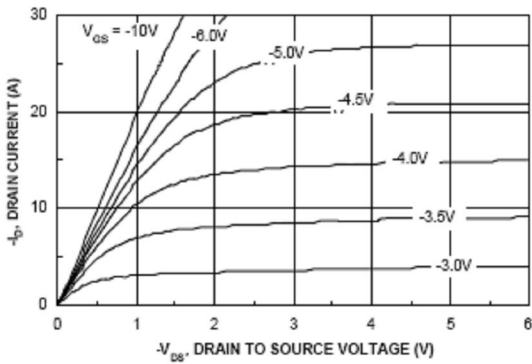


Figure 1. On-Region Characteristics.

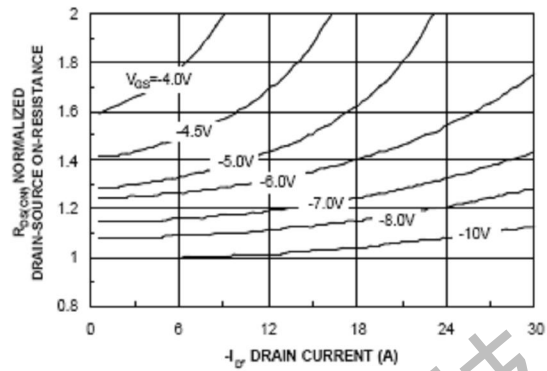


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

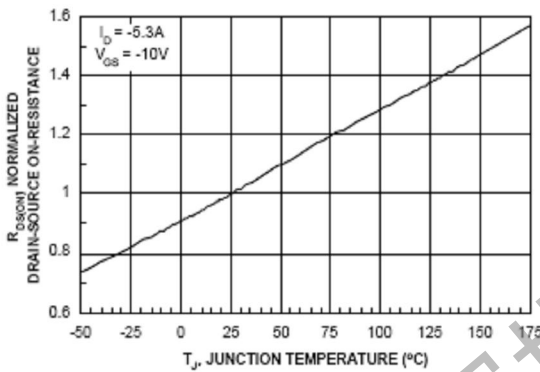


Figure 3. On-Resistance Variation with Temperature.

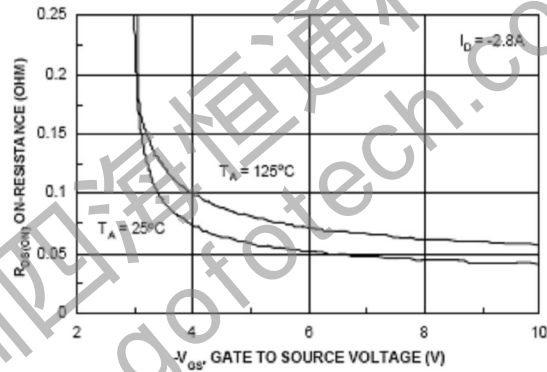


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

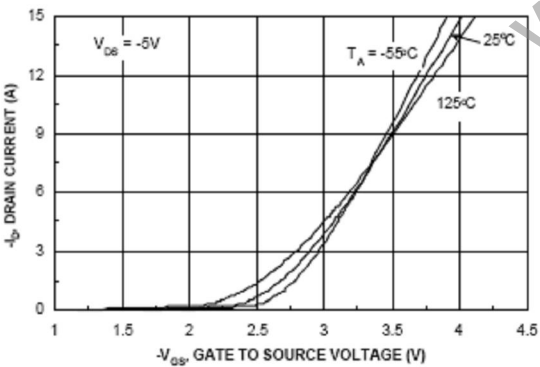


Figure 5. Transfer Characteristics.

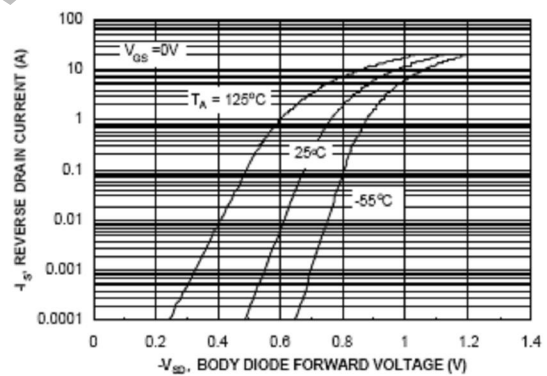


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

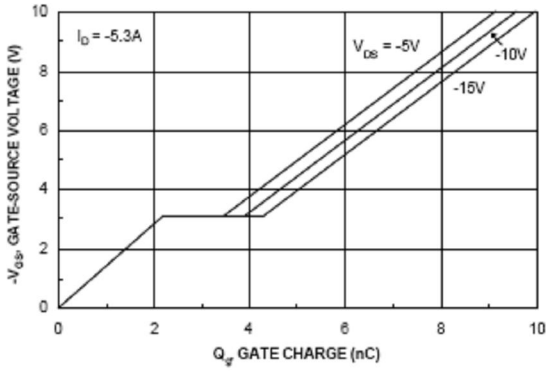


Figure 7. Gate Charge Characteristics.

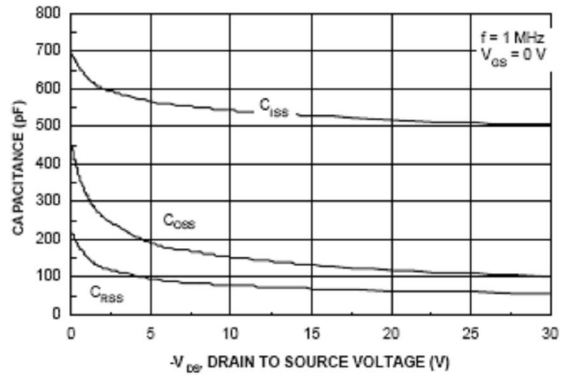


Figure 8. Capacitance Characteristics.

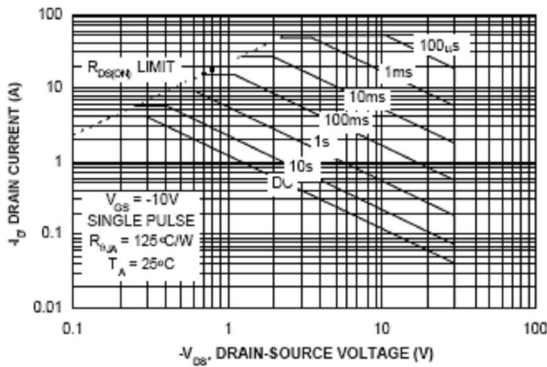


Figure 9. Maximum Safe Operating Area.

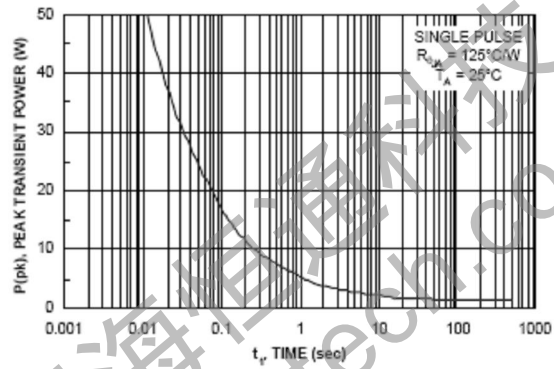


Figure 10. Single Pulse Maximum Power Dissipation.

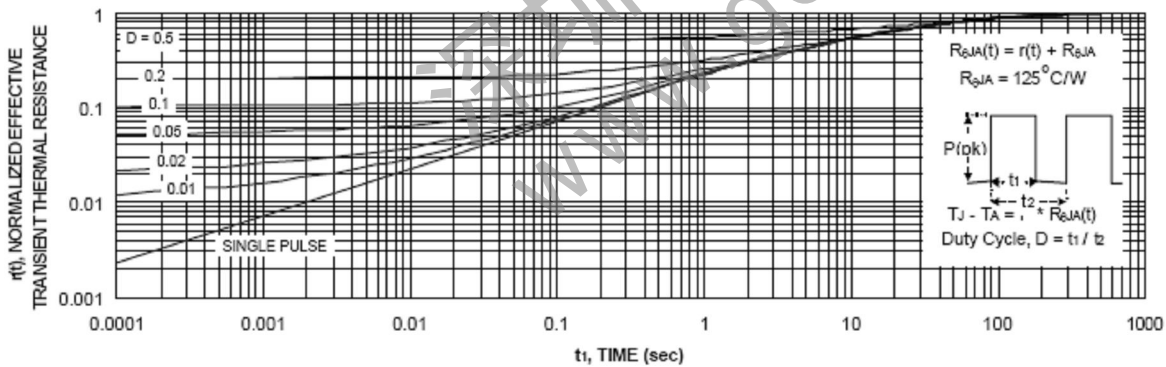
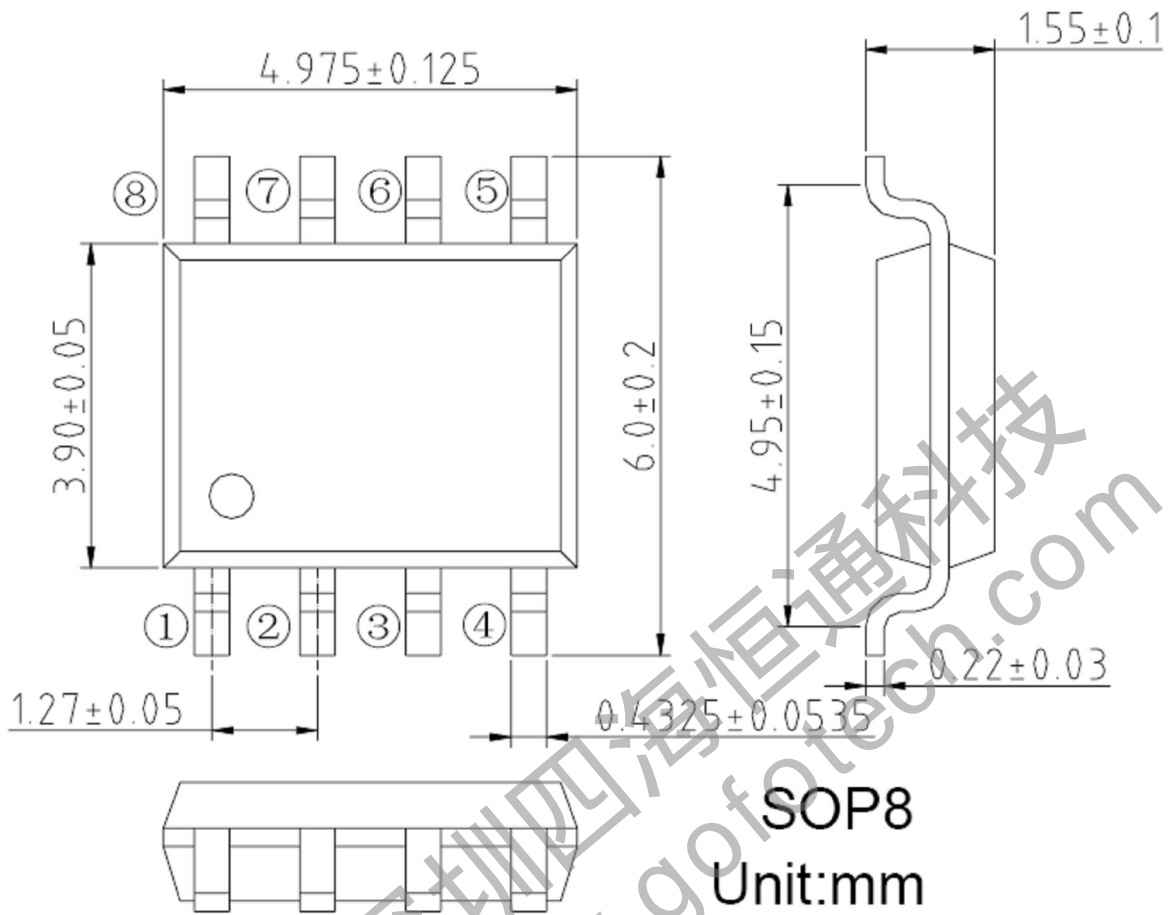


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

Package Information :



深圳四海恒通科技
www.gofotech.com

- The information described herein is subject to change without notice.
- Nanjing Micro One Electronics Inc is not responsible for any problems caused by circuits or diagrams described herein whose related industrial properties, patents, or other rights belong to third parties. The application circuit examples explain typical applications of the products, and do not guarantee the success of any specific mass-production design.
- Use of the information described herein for other purposes and/or reproduction or copying without the express permission of Nanjing Micro One Electronics Inc is strictly prohibited.
- The products described herein cannot be used as part of any device or equipment affecting the human body, such as exercise equipment, medical equipment, security systems, gas equipment, or any apparatus installed in airplanes and other vehicles, without prior written permission of Nanjing Micro One Electronics Inc.
- Although Nanjing Micro One Electronics Inc exerts the greatest possible effort to ensure high quality and reliability, the failure or malfunction of semiconductor products may occur. The user of these products should therefore give thorough consideration to safety design, including redundancy, fire-prevention measures, and malfunction prevention, to prevent any accidents, fires, or community damage that may ensue.